Application No. 10/634,558 Docket No. 15436.434.3.1 Reply to Office Action mailed May 17, 2005

(Currently Amended) [[25.]] 24. The semiconductor laser according to invention of claim [[22]] 21, wherein the alloy layers are about 24Å thick.

(New) The invention of claim 1, wherein each layer of stabilization material comprises GaAs.